

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1 (canceled)

2 (currently amended): A semiconductor integrated circuit device according to claim ~~1~~4, further comprising a power supply terminal to which an external power supply voltage is applied, wherein a transistor connected directly to the power supply terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

3 (currently amended): A semiconductor integrated circuit device according to claim ~~1~~4, further comprising a power supply terminal to which an external power supply voltage is applied and a ground terminal, wherein a transistor having a current path connected between the power supply terminal and the ground terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

Claim 4 (canceled)

5 (currently amended): A semiconductor integrated circuit device according to claim ~~4~~14, wherein a transistor included in the interface circuit and connected directly to a power supply terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

6 (previously presented): A semiconductor integrated circuit device according to claim 5, wherein a transistor included in the interface circuit and having a current path connected between the power supply terminal and a ground terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

Claims 7-13 (canceled)

14 (currently amended): ~~A semiconductor integrated circuit device according to claim 13, A~~
semiconductor integrated circuit device comprising:

a semiconductor substrate on which a plurality of transistors having gate insulation films
of three or more different thicknesses are formed;

an input/output terminal formed on the semiconductor substrate, wherein a transistor
physically connected directly to the input/output terminal is one of the transistors other than a
transistor having the thinnest gate insulation film;

an interface circuit connected to the input/output terminal, wherein a transistor included
in the interface circuit and connected directly to the input/output terminal is one of the transistors
other than the transistor having the thinnest gate insulation film, and wherein said interface
circuit includes a level shifter and an output buffer circuit; and

a regulator circuit, said level shifter converting a lowered potential level signal obtained
from the regulator circuit into a power supply voltage level signal to be supplied to an external
terminal,

wherein a transistor included in the level shifter and a device directly receiving the
lowered potential level signal is the transistor having the thinnest gate insulation film.

Claims 15-21 (canceled)

22 (currently amended): A semiconductor integrated circuit device according to claim 24~~27~~,
further comprising a power supply terminal to which an external power supply voltage is
applied, wherein a transistor connected directly to the power supply terminal is one of the
transistors other than the transistor having the thinnest gate insulation film.

23 (currently amended): A semiconductor integrated circuit device according to claim 24~~27~~,
further comprising a power supply terminal to which an external power supply voltage is applied
and a ground terminal, wherein a transistor having a current path connected between the power
supply terminal and the ground terminal is one of the transistors other than the transistor having
the thinnest gate insulation film.

Claim 24 (canceled)

25 (currently amended): A semiconductor integrated circuit device according to claim 24~~27~~, wherein a transistor included in the interface circuit and connected directly to a power supply terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

26 (previously presented): A semiconductor integrated circuit device according to claim 25, wherein a transistor included in the interface circuit and having a current path connected between the power supply terminal and a ground terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

27 (currently amended): ~~A semiconductor integrated circuit device according to claim 24, A~~
semiconductor integrated circuit device comprising:

a semiconductor substrate on which a plurality of transistors having gate insulation films of three or more different thicknesses are formed;

an input/output terminal formed on the semiconductor substrate, wherein a transistor connected directly to the input/output terminal, absent any intervening elements, is one of the transistors other than a transistor having the thinnest gate insulation film; and

an interface circuit connected to the input/output terminal, wherein a transistor included in the interface circuit and connected directly to the input/output terminal is one of the transistors other than the transistor having the thinnest gate insulation film, wherein said interface circuit includes an input buffer circuit.

Claims 28-30 (canceled)

31 (currently amended): ~~A semiconductor integrated circuit device according to claim 30, A~~
semiconductor integrated circuit device comprising:

a semiconductor substrate on which a plurality of transistors having gate insulation films of three or more different thicknesses are formed;

an input/output terminal formed on the semiconductor substrate, wherein a transistor connected directly to the input/output terminal, absent any intervening elements, is one of the transistors other than a transistor having the thinnest gate insulation film;

an interface circuit connected to the input/output terminal, wherein a transistor included in the interface circuit and connected directly to the input/output terminal is one of the transistors other than the transistor having the thinnest gate insulation film, and wherein said interface circuit includes a level shifter and an output buffer circuit; and

a regulator circuit, said level shifter converting a lowered potential level signal obtained from the regulator circuit into a power supply voltage level signal to be supplied to an external terminal,

wherein a transistor included in the level shifter and a device directly receiving the lowered potential level signal is the transistor having the thinnest gate insulation film.

Claim 32 (canceled)

33 (currently amended): A semiconductor integrated circuit device according to claim 3242, further comprising a power supply terminal to which an external power supply voltage is applied, wherein a transistor connected directly to the power supply terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

34 (currently amended): A semiconductor integrated circuit device according to claim 3242, further comprising a power supply terminal to which an external power supply voltage is applied and a ground terminal, wherein a transistor having a current path connected between the power supply terminal and the ground terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

Claim 35 (canceled)

36 (currently amended): A semiconductor integrated circuit device according to claim ~~35~~42, wherein a transistor included in the interface circuit and connected directly to a power supply terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

37 (previously presented): A semiconductor integrated circuit device according to claim 36, wherein a transistor included in the interface circuit and having a current path connected between the power supply terminal and a ground terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

Claims 38-41 (canceled)

42 (currently amended): ~~A semiconductor integrated circuit device according to claim 41, A~~
semiconductor integrated circuit device comprising:

a semiconductor substrate on which a plurality of transistors having gate insulation films of three or more different thicknesses are formed;

an input/output terminal formed on the semiconductor substrate, wherein a transistor always connected directly to the input/output terminal is one of the transistors other than a transistor having the thinnest gate insulation film;

an interface circuit connected to the input/output terminal, wherein a transistor included in the interface circuit and connected directly to the input/output terminal is one of the transistors other than the transistor having the thinnest gate insulation film, and wherein said interface circuit includes a level shifter and an output buffer circuit; and

a regulator circuit, said level shifter converting a lowered potential level signal obtained from the regulator circuit into a power supply voltage level signal to be supplied to an external terminal,

wherein a transistor included in the level shifter and a device directly receiving the lowered potential level signal is the transistor having the thinnest gate insulation film.

43 (new): A semiconductor integrated circuit device according to claim 31, further comprising a power supply terminal to which an external power supply voltage is applied, wherein a transistor

connected directly to the power supply terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

44 (new): A semiconductor integrated circuit device according to claim 31, further comprising a power supply terminal to which an external power supply voltage is applied and a ground terminal, wherein a transistor having a current path connected between the power supply terminal and the ground terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

45 (new): A semiconductor integrated circuit device according to claim 31, wherein a transistor included in the interface circuit and connected directly to a power supply terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

46 (new): A semiconductor integrated circuit device according to claim 45, wherein a transistor included in the interface circuit and having a current path connected between the power supply terminal and a ground terminal is one of the transistors other than the transistor having the thinnest gate insulation film.